Influence of the out-of-band light absorption on temperature increase of a pellicle in EUVL

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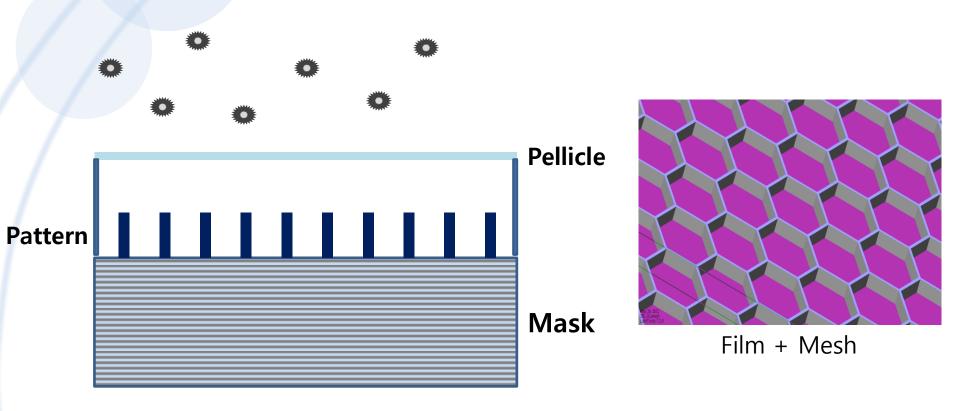
Introduction

- Pellicle
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 - Thermal behavior of the film
 - Thermal behavior of the mesh
- Conclusion



What is the pellicle?

• Pellicle: Thin film supported by the mesh structure

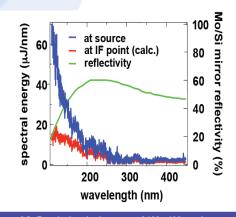


A pellicle protects the mask from contamination!



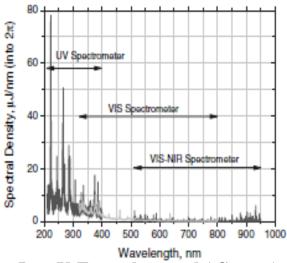
Additional OoB Radiation

➤ Out-of-band light spectrum of the EUV source



Energy of OoB emission, in the range of 100 - 400 nm, is 2.78 mJ@source, corresponding to 1.14 mJ@IF or 22.1 % of 13.5-nm EUV. That is about three-times of the joint requirement value of 3-7%

<H. Nishimura et al.(ILE Osaka Univ.), EUVL symposium, Sapporo (2007)>



< Igor V. Fomenkov et al.(Cymer,) SPIE 021110 (2012) >

| Performance indicator | Specification (production tool) | |
|-------------------------------|---|--|
| Maximum IR load into scanner | 1% of EUV power in the wafer level | |
| Maximum DUV load into scanner | 10-100% of EUV power in the wafer level | |

< Roel Moors et al. (ASML), SPIE 021102 (2012) >

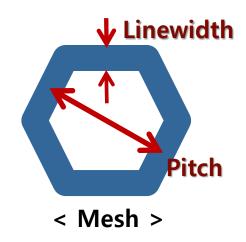


Thermal Modeling

Appearance conditions of the pellicle

- Film: 50 nm thickness

Mesh: 50 μm thickness,
3 μm linewidth,
100 μm pitch





Thermal Modeling

EUV (13.5nm) +OoB (DUV+UV+Visible+IR) Pellicle -Frame Pattern Mask

➤ Exposure conditions

| Exposure slit area | 10 cm ² | |
|--------------------|--------------------|--|
| Exposure slit time | 10 ms | |
| EUV power | 50 W | |
| OoB ratio | | |
| (% of EUV power) | 0 – 100 % | |

➤ Absorption ratio of the pellicle

| | Film | Mesh |
|---------------------|------|------|
| EUV (13.5nm) | 8% | 100% |
| OoB (DUV~IR) | 100% | 100% |



Thermal Modeling

> Consider radiation cooling in heating process

$$c \cdot m \cdot \frac{dT}{dt} = \alpha \cdot P - \varepsilon \cdot \sigma \cdot A(T^4 - T_S^4)$$

heating term due to absorption of EUV beam

α : Absorption ratio

ε: Emissivity

σ : Stefan's constant

c : Specific heat

cooling term due to heat transfer of radiation mechanism

m: Mass

A: Area of a surface of material

T: Temperature of material

 T_s : Surrounding temperature

X The dominant cooling process is radiation since :

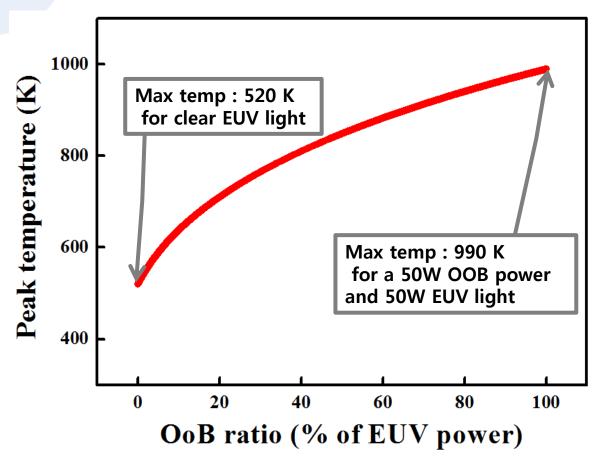
- Conduction: too small cross-section area

- Convection: vacuum



Result - Film

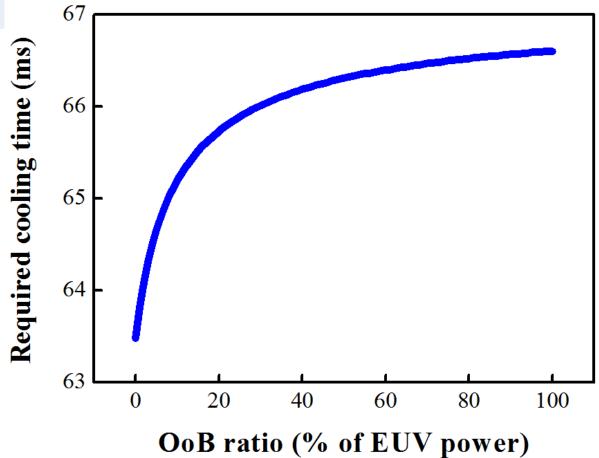
➤ The peak temperature of the film as a function of the OoB radiation ratio.





Result - Film

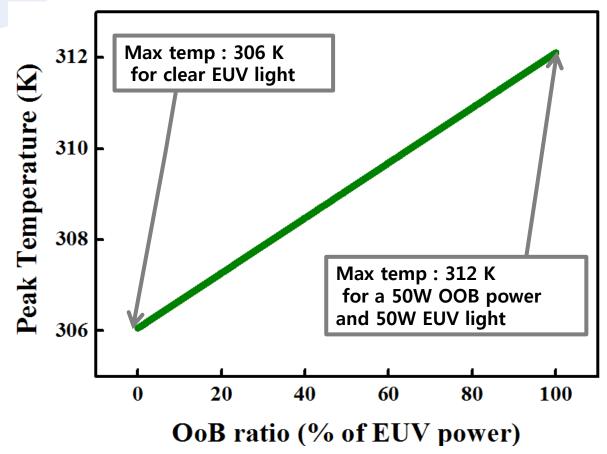
➤ Required cooling time of the film as a function of the OoB radiation ratio.





Result - Mesh

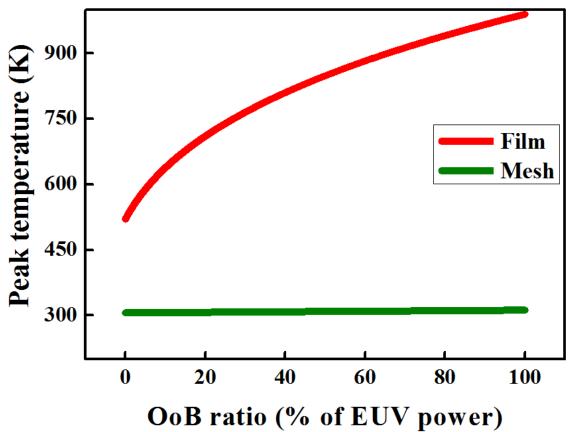
➤ The peak temperature of the mesh as a function of the OoB radiation ratio.





Result - Mesh

Comparison of the peak temperature between the film and the mesh for additional OoB light absorption.





Conclusion

- Thermal behavior of the pellicle was calculated using the modified heat transfer equation.
- ➤ For 50 W of the OoB incident power and 50 W of the EUV light power, the highest temperature of the film is 990 K which is 470 K higher than that for 50 W of EUV light power only, and the required cooling time is less than 67 ms which is similar to that without EUV. Our results suggest that the thermal problem due to the EUV light even with the additional OoB light absorption can be minimized if the interval between EUV light exposures is longer than 70 ms.
- ➤ The peak temperature of the mesh is linearly proportional to additional OoB radiation but it was much smaller than the peak temperature of the film. Therefore the thermal problems of the mesh can be neglected.
- ➤ The temperature difference between the film and the mesh may induce another problems, e.g. pellicle deformation. Therefore it needs more study about the impact of the temperature difference on the pellicle.